PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Shields & Ko

Assignee: Advanced Micro Devices, Inc.

Title: A SACRIFICIAL TiN ARC LAYER FOR INCREASED PAD ETCH THROUGHPUT

Serial No.: 09/208,325 Filed: 12/9/98

Examiner: T. Nguyen Group Art Unit:2813

Attorney Docket No.: D730

Anthem, Arizona
July 2, 2000

COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231

AMENDMENT

Sir:

In response to the Examiner's Office Action of 4/6/00, please amend the above-cited application as follows.

In the Specification

On page 1, line 34, please change "over" to read - - under- -.

In the Claims

Please amend the claims as follows. For the convenience of the Examiner, claims not amended are reproduced below in reduce font.

Please amend Claim 1 as follows:

1. (Once amended) A method of manufacturing a semiconductor device, wherein the method comprises:

forming a final layer of metal on a layer of interlayer dielectric in the semiconductor device;

forming a layer of TiN on the final layer of metal;

forming a first layer of photoresist on the layer of TiN;

patterning and developing the first layer of photoresist exposing portions of the layer of TiN;

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